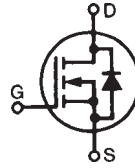


# High Voltage Power MOSFET

**IXTU01N100**  
**IXTY01N100**

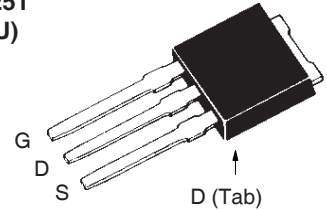
$V_{DSS} = 1000V$   
 $I_{D25} = 100mA$   
 $R_{DS(on)} \leq 80\Omega$

N-Channel Enhancement Mode

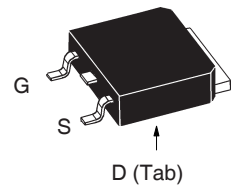


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	1000	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	100	mA
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	400	mA
$P_D$	$T_C = 25^\circ C$	25	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$F_C$	Mounting force	1.13 / 10	Nm/lb.in.
<b>Weight</b>	TO-251	0.40	g
	TO-252	0.35	g

TO-251  
(IXTU)



TO-252  
(IXTY)



G = Gate      D = Drain  
S = Source      Tab = Drain

## Features

- International Standard Packages
- Fast Switching Times
- Avalanche Rated
- $R_{ds(on)}$  HDMOS™ Process
- Rugged Polysilicon Gate Cell structure

## Advantages

- High Power Density
- Space Savings

## Applications

- Level Shifting
- Triggers
- Solid State Relays
- Current Regulators

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 25\mu A$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 25\mu A$	2.0		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 50$ nA
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			10 $\mu A$ 200 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 50mA$ , Note 1		60	80 $\Omega$

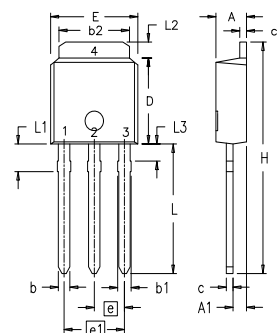
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 50\text{mA}$ , Note 1		0.16	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		54.0	pF
$C_{oss}$			6.9	pF
$C_{rss}$			2.0	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 50\text{mA}$ $R_G = 50\Omega$ (External)		12	ns
$t_r$			12	ns
$t_{d(off)}$			40	ns
$t_f$			28	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 50\text{mA}$		6.9	nC
$Q_{gs}$			1.8	nC
$Q_{gd}$			3.0	nC
$R_{thJC}$			5	$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			100 mA
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			300 mA
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.8 V
$t_{rr}$	$I_F = 0.75\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ , $V_R = 25\text{V}$			1.5 $\mu\text{s}$

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

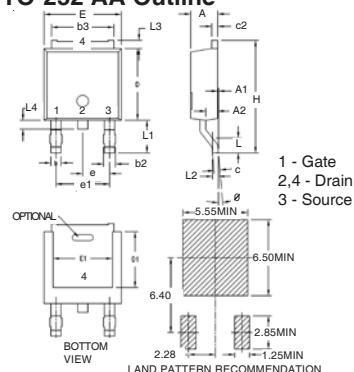
### TO-251 Outline



1. Gate 2. Drain  
3. Source 4. Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.19	2.38	.086	.094
A1	0.89	1.14	0.35	.045
b	0.64	0.89	.025	.035
b1	0.76	1.14	.030	.045
b2	5.21	5.46	.205	.215
c	0.46	0.58	.018	.023
c1	0.46	0.58	.018	.023
D	5.97	6.22	.235	.245
E	6.35	6.73	.250	.265
e	2.28	BSC	.090	BSC
e1	4.57	BSC	.180	BSC
H	17.02	17.78	.670	.700
L	9.89	9.65	.350	.380
L1	1.91	2.28	.075	.090
L2	0.89	1.27	.035	.050

### TO-252 AA Outline



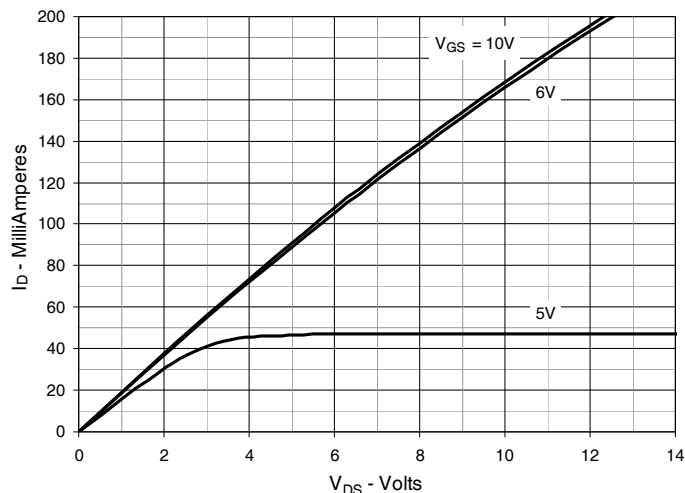
- 1 - Gate  
2, 4 - Drain  
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.086	.094	2.19	2.38
A1	0	.005	0	0.12
A2	.038	.046	0.97	1.17
b	.025	.035	0.64	0.89
b2	.030	.045	0.76	1.14
b3	.200	.215	5.08	5.46
c	.018	.024	0.46	0.61
c2	.018	.023	0.46	0.58
D	.235	.245	5.97	6.22
D1	.180	.205	4.57	5.21
E	.250	.265	6.35	6.73
E1	.170	.205	4.32	5.21
e	.090 BSC		2.28 BSC	
e1	.180 BSC		4.57 BSC	
H	.370	.410	9.40	10.42
L	.055	.070	1.40	1.78
L1	.100	.115	2.54	2.92
L2	.020 BSC		0.50 BSC	
L3	.025	.040	0.64	1.02
L4	.025	.040	0.64	1.02
θ	0°	10°	0°	10°

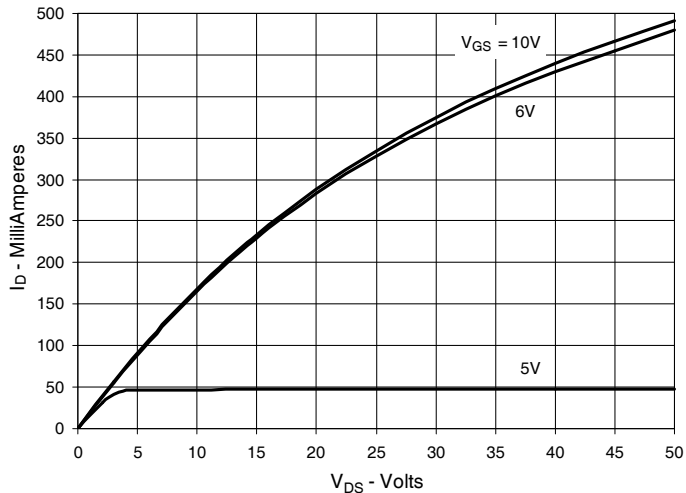
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

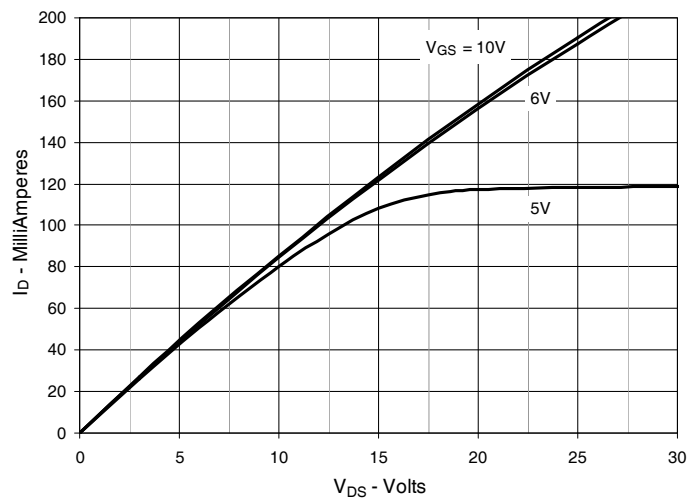
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



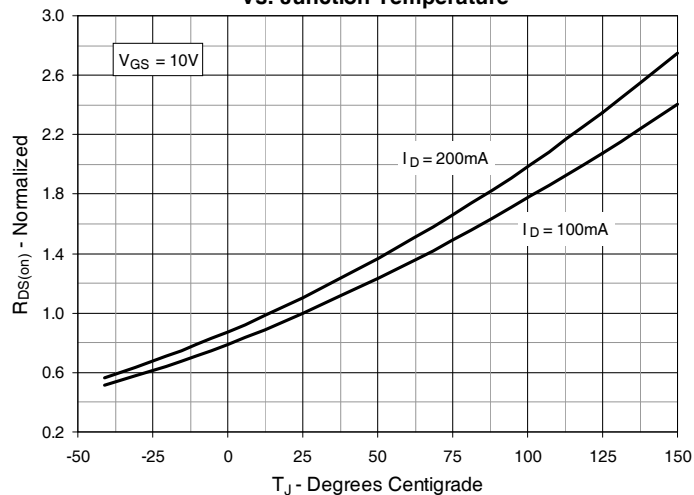
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



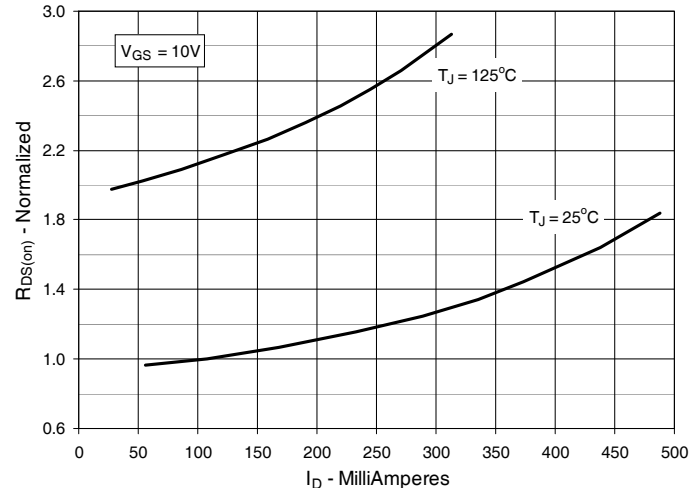
**Fig. 2. Output Characteristics @  $T_J = 125^\circ\text{C}$**



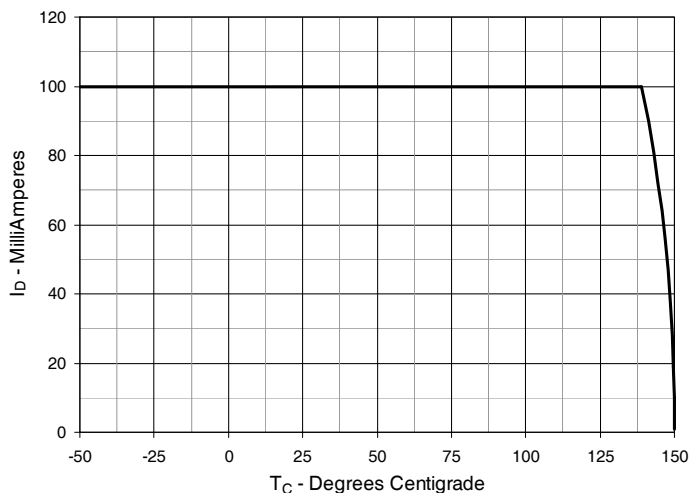
**Fig. 3.  $R_{DS(on)}$  Normalized to  $I_D = 50\text{mA}$  Value vs. Junction Temperature**



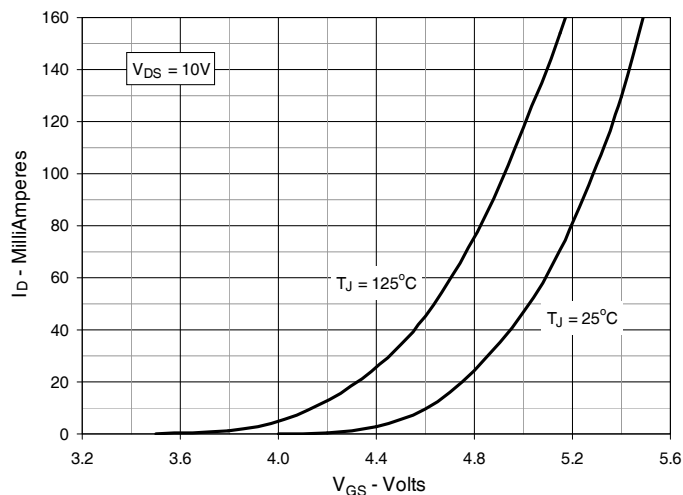
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 50\text{mA}$  Value vs. Drain Current**



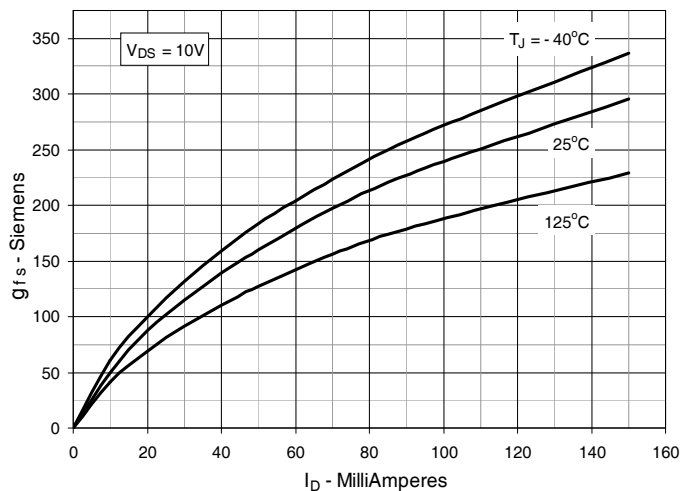
**Fig. 5. Maximum Drain Current vs. Case Temperature**



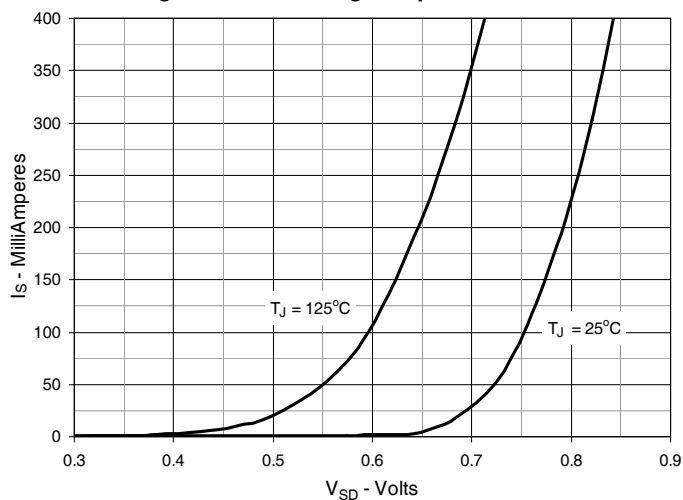
**Fig. 7. Input Admittance**



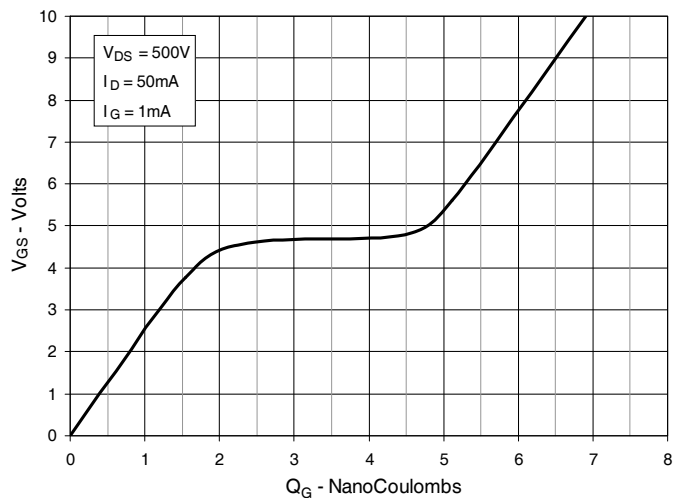
**Fig. 8. Transconductance**



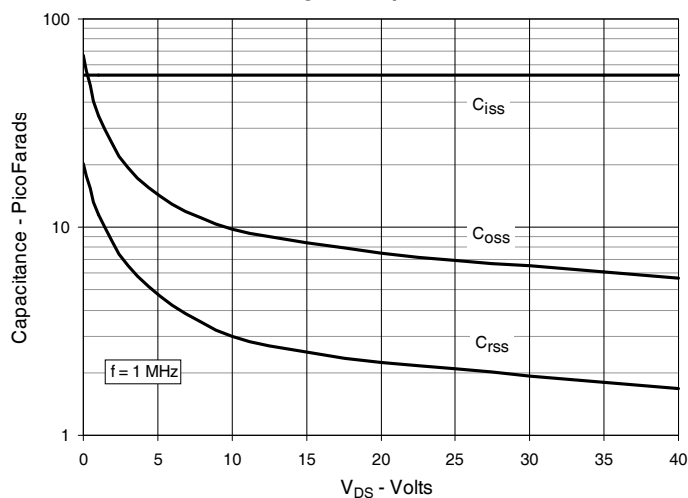
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



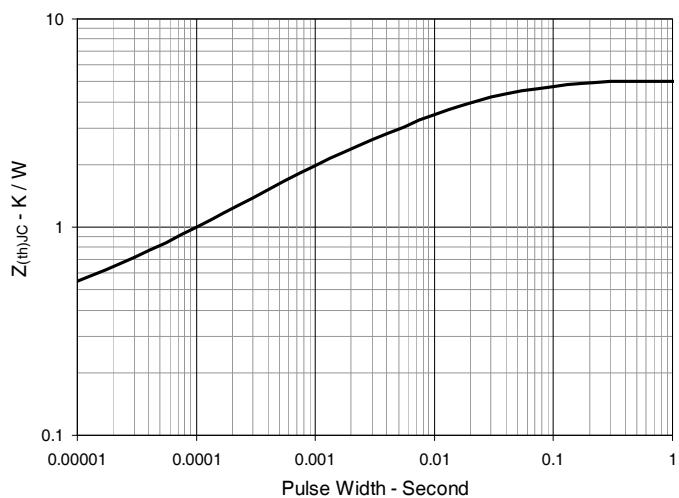
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**





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